NEC

NPN SILICON TRANSISTOR 2SC2688

DESCRIPTION

The 2SC2688 is designed for use in Color TV chroma output

circuits.

FEATURES

• High Electrostatic-Discharge-Resistance. (E-B reverse bias,

C = 2300 pF) ESDR: TYP. 1000 V

Low C_{re}, High f_T

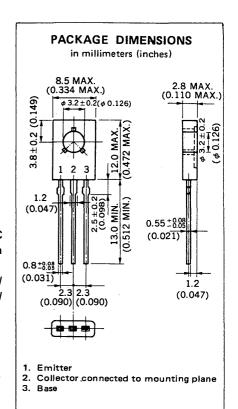
Maximum Temperatures

 $C_{re} \le 3.0 \, pF \, (V_{CB} = 30 \, V)$

 $f_T \geqq 50 \text{ MHz} \text{ (V}_{\text{CE}} = 30 \text{ V, I}_{\text{E}} = -10 \text{ mA)}$

ABSOLUTE MAXIMUM RATINGS

V_{CBO}	Collector to Base Voltage	300	٧
V _{CEO}	Collector to Emitter Voltage	300	V
V _{EBO}	Emitter to Base Voltage	5.0	٧
Ic	Collector Current	200	mΑ



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE	DC Current Gain	40	80	250		V _{CE} = 10 V, I _C = 10 mA*
fT	Gain Bandwidth Product	50	80		MHz	$V_{CE} = 30 \text{ V}, I_{E} = -10 \text{ mA}$
C _{re}	Feedback Capacitance			3.0	pF	$V_{CB} = 30 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$
ІСВО	Collector Cutoff Current			100	nΑ	$V_{CB} = 200 V, I_{E} = 0$
I _{EBO}	Emitter Cutoff Current			100	nΑ	$V_{EB} = 5.0 V, I_{C} = 0$
V _{CE(sat)}	Collector Saturation Voltage			1.5	V	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$

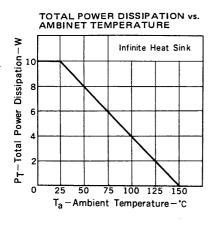
^{*}Pulsed PW \leq 350 μ s, Duty Cycle \leq 2 %

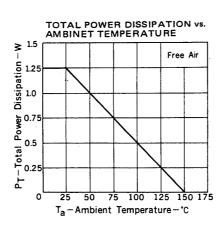
Classification of hFE

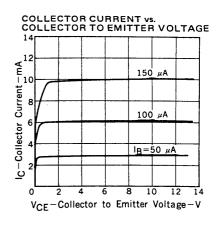
Rank	N	М	L	к
Range	40 to 80	60 to 120	100 to 200	160 to 250

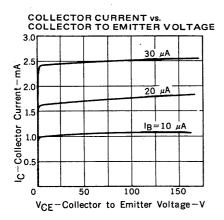
Test Conditions : $V_{CE} = 10 \text{ V}$, $I_{C} = 10 \text{ mA}$

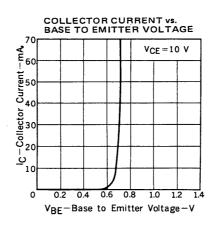
TYPICAL CHARACTERISTICS (Ta = 25 °C)

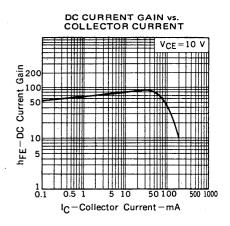


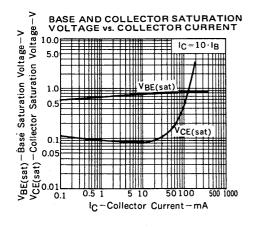


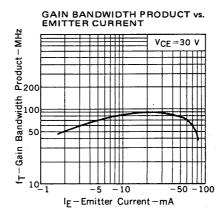


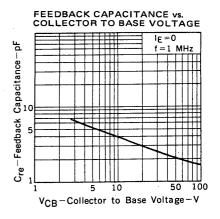




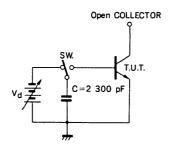








BURNOUT TEST CIRCUIT BY DISCHARGE OF CAPACITOR



TEST CONDITION

- E-B reverse bias
 C = 2300 pF
 Apply one shot pulse to T.U.T. (Transistor Under the Test) by SW.

JUDGEMENT

REJECT; BV_{EBO} waveform defect As a result if T.U.T. is not rejected, apply higher voltage to capacitor and test again.